FPF2280
Over-Voltage Protection Load Switch

Features

- Surge Protection
  - IEC 61000-4-5: > 100 V
- Over-Voltage Protection (OVP)
- Over-Temperature Protection (OTP)
- ESD Protection
  - Human Body Model (HBM): > 3.5 kV
  - Charged Device Model (CDM): > 2 kV
  - IEC 61000-4-2 Air Discharge: > 15 kV
  - IEC 61000-4-2 Contact Discharge: > 8 kV

Applications

- Mobile Handsets and Tablets
- Portable Media Players
- MP3 Players

Description

The FPF2280 features a low-R_{ON} internal FET and an operating range of 2.5 V_{DC} to 5.5 V_{DC} (absolute maximum of 29 V_{DC}). An internal clamp is capable of shunting surge voltages >100 V, protecting downstream components and enhancing system robustness. The FPF2280 features over-voltage protection that powers down the internal FET if the input voltage exceeds the OVP threshold. The OVP threshold is adjustable with optional external resistors. Over-temperature protection also powers down the device at 130°C (typical). Exceptionally low off-state current (<1 μA maximum) facilitates compliance with standby power requirements.

The FPF2280 is available in a fully “green” compliant 1.3 mm × 1.8 mm Wafer-Level Chip-Scale Package (WLCSP) with backside laminate.

Related Resources

- http://www.onsemi.com/

Ordering Information

Part Number	Operating Temperature Range	Top Mark	Package	Packing Method
FPF2280BUCX-F130	-40°C – 105°C	HC	12-Ball, 0.4 mm Pitch WLCSP	Tape & Reel

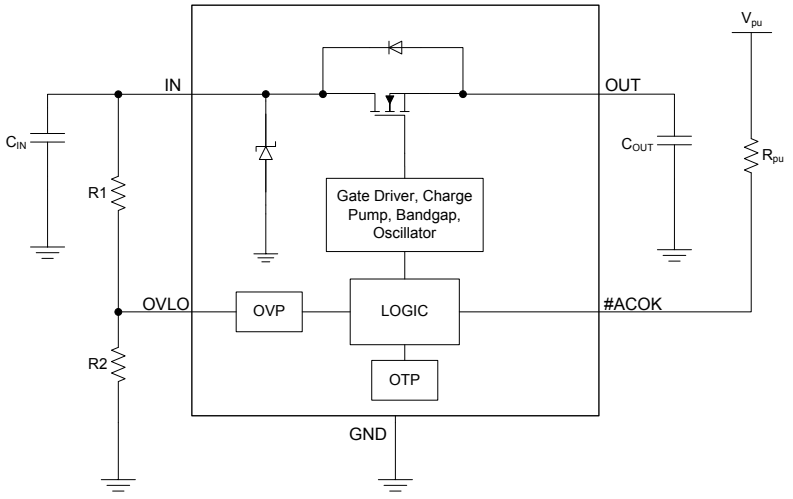

Figure 1. Functional Block Diagram

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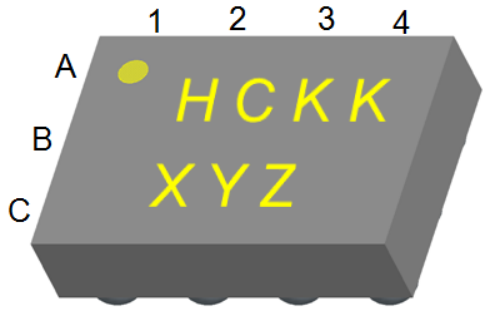
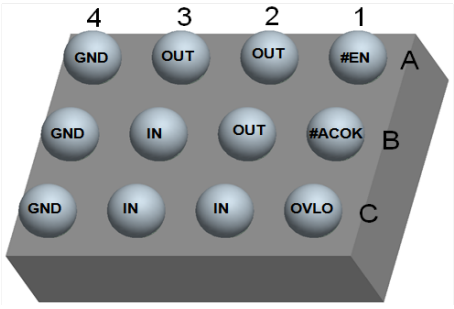
Publication Order Number:
FPF2280BUCX-F130/D

Pin Configuration





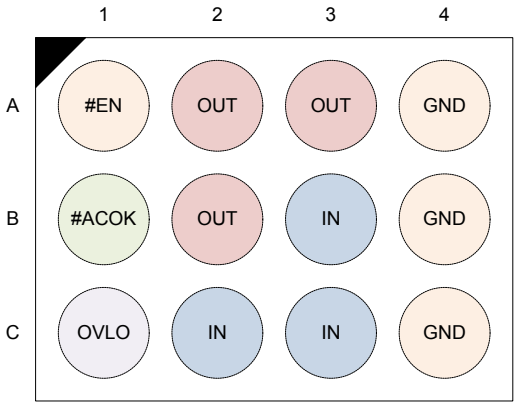


Figure 2. Pin Configuration (Top View)

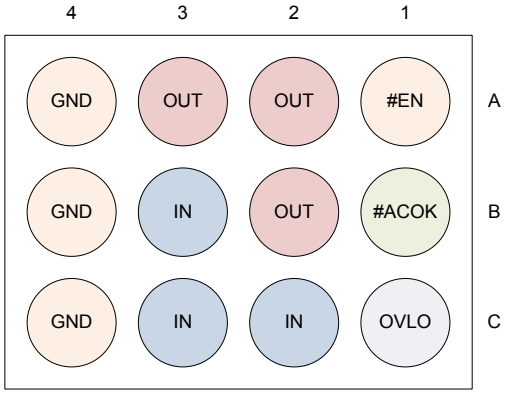


Figure 3. Pin Configuration (Bottom View)

Pin Definitions

Name	Bump	Type	Description		
IN	B3, C2, C3	Input/Supply	Switch Input and Device Supply		
OUT	A2, A3, B2	Output	Switch Output to Load		
#ACOK	B1	Output (Open Drain)	Power Good	1	$V_{IN} < V_{IN\_min}$ or $V_{IN} \geq V_{OVLO}$
				0	Voltage Stable
#EN	A1	Input	Device Enable (Active LOW)		
OVLO	C1	Input	Over-Voltage Lockout Adjustment Pin		
GND	A4, B4, C4	Supply	Device Ground		

Over-Voltage Lockout (OVLO) Calculation

OVLO can be set externally and override default OVP. By connecting an external resistor-driver to the OVLO pin. Equation (1) can produce the desired trip voltage and resistor values.

$$V_{IN\_OLVO} = V_{OVLO\_TH} \times [1 + R1/R2] \quad (1)$$

Recommended minimum R1 = 1 MΩ.

On-The-Go (OTG) Functionality

During OTG operation, the FPF2280 is initially disabled and the power FET's bulk diode is forward biased. The bulk diode represents ~0.7 V drop across the device, which remains until the V_IN voltage increases past 2.5 V, when the device is fully enabled. While the device is disabled and the body diode is forward biased, the max DC current through the diode is 1.8 A. This current is limited by the thermal performance of the device (0.7 Vx 1.8 A = 1.36 W). This current should be transient; the #EN pin must be pulled LOW to ensure the device fully enables. The transient should not exceed the RC time constant of the C_IN and C_OUT capacitors. At the system level, over-voltage and current protection should be provided outside the FPF2280.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter		Min.	Max.	Unit
V_{IN}	V_IN to GND & V_IN to V_OUT = GND or Float		-0.3	29.0	V
V_{OUT}	V_OUT to GND		-0.3	V_{IN} + 0.3	V
V_{OVLO}	OVLO to GND		-0.3	24.0	V
$V_{\#EN\_ACOK}$	Maximum DC Voltage Allowed on #EN or ACOK Pin			6	V
I_{IN}	Switch I/O Current (Continuous)			4.5	A
t_{PD}	Total Power Dissipation at T_A = 25°C			1.48	W
T_{STG}	Storage Temperature Range		-65	+150	°C
T_J	Maximum Junction Temperature			+150	°C
T_L	Lead Temperature (Soldering, 10 Seconds)			+260	°C
Θ_{JA}	Thermal Resistance, Junction-to-Ambient[1] (1-in.^{2} Pad of 2-oz. Copper)			84.1	°C/W
ESD	IEC 61000-4-2 System ESD	Air Gap	15.0		kV
		Contact	8.0		
	Human Body Model, ANSI/ESDA/JEDEC JS-001-2012	All Pins	3.5		
	Charged Device Model, JESD22-C101	All Pins	2.0		
Surge	IEC 61000-4-5, Surge Protection	V_{IN}	100		V

Note:

1. Measured using 2S2P JEDEC std. PCB.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Max.	Unit
V_{IN}	Supply Voltage	2.5	20.0	V
T_A	Operating Temperature	-40	+105	ºC

Electrical Characteristics

T_A = -40°C to 105°C unless otherwise indicated. Typical values are V_{IN} = 5.0 V, $I_{IN} \le 3$ A, C_{IN} = 0.1 µF and T_A = 25°C.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{IN_CLAMP}	Input Clamping Voltage	I_{IN} = 10 mA		35		V
I_Q	Input Quiescent Current	V_{IN} = 5 V, #EN = 0 V		58	100	µA
I_{IN_Q}	OVLO Supply Current	V_{OVLO} = 3 V, V_{IN} = 5 V, V_{OUT} = 0 V		63	100	µA
V_{IN_OVLO}	Internal Over-Voltage Trip Level	V_{IN} Rising, OVLO = GND	6.6	6.8	7.0	V
		V_{IN} Falling	6.2			V
V_{OVLO_TH}	OVLO Set Threshold	V_{IN} = 2.5 V to V_{OVLO}	1.12	1.20	1.24	V
V_{OVLO_RNG}	Adjustable OVLO Threshold Range	V_{IN} = 2.5 V to V_{OVLO}	4		20	V
V_{OVLO_SELECT}	External OVLO Select Threshold			0.30	0.28	V
R_{ON}	Resistance from V_{IN} to V_{OUT}	V_{IN} = 5 V, I_{OUT} = 1 A. T_A = 25ºC		30	39	mΩ
C_{OUT}	OUT Load Capacitance(2)	V_{IN} = 5 V			1000	µF
I_{OLVO}	OVLO Input Leakage Current	V_{OVLO} = V_{OVLO_TH}	-100		100	nA
T_{SDN}	Thermal Shutdown(2)			130		°C
T_{SDN_HYS}	Thermal Shutdown Hysteresis(2)			20		°C
Digital Signals						
V_{OL}	#ACOK Output Low Voltage	$V_{I/O}$ = 3.3 V, I_{SINK} = 1 mA			0.4	V
VIH_#EN	Enable HIGH Voltage	V_{IN} = 2.5 V to V_{OVLO}	1.2			V
VIL_#EN	Enable LOW Voltage	V_{IN} = 2.5 V to V_{OVLO}			0.5	V
I_{ACOK_LEAK}	#ACOK Leakage Current	$V_{I/O}$ = 3.3 V, #ACOK Deasserted, #EN = 0 V	-0.5		0.5	µA
#EN_Leak	#EN Leakage Current	V_{IN} = 5.0 V, V_{OUT} = Float	-1.0		1.0	µA
Timing Characteristics						
t_{DEB}	Debounce Time	Time from 2.5 V < V_{IN} < V_{IN_OVLO} to V_{OUT} = 0.1 × V_{IN}		15		ms
t_{START}	Soft-Start Time	Time from V_{IN} = V_{IN_min} to 0.2 × #ACOK, V_{IO} = 1.8 V with 10 kΩ Pull-up Resistor		30		ms
t_{ON}	Switch Turn-On Time	V_{IN} = 5 V, R_L = 100 Ω, V_{OUT} from 0.1 × V_{IN} to 0.9 × V_{IN}, C_{LOAD} = 100 µF		2		ms
t_{OFF}	Switch Turn-Off Time(2)	R_L = 100 Ω, C_L = 0 µF, V_{IN} > V_{OVLO} to V_{OUT} = 0.8 × V_{IN}		125		ns

Note:

2. Guaranteed by characterization and design.

Timing Diagrams

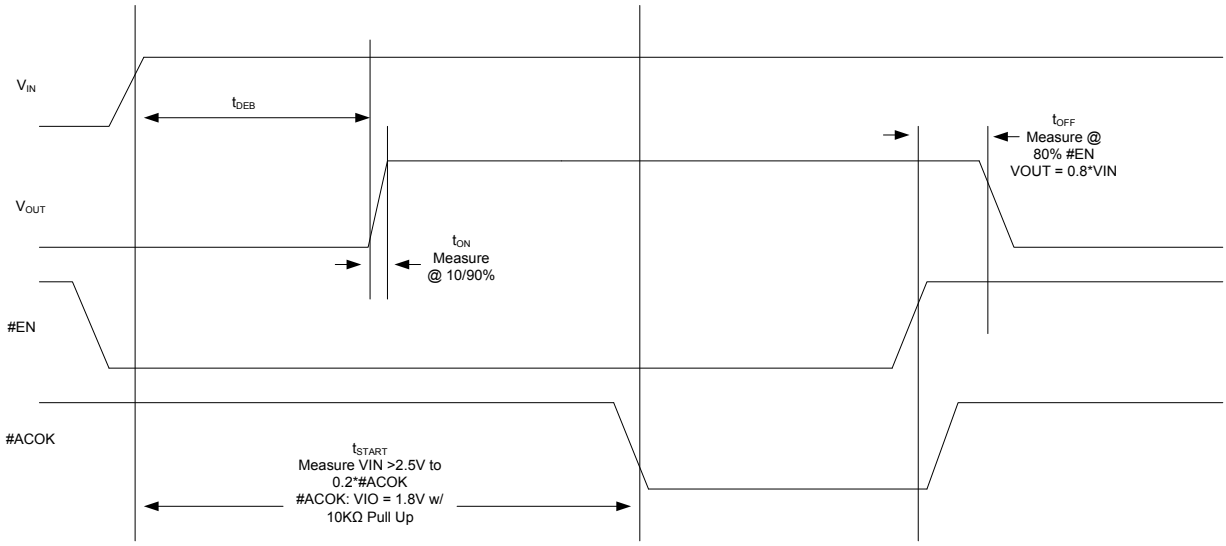


Figure 4. Timing for Power Up and Normal Operation

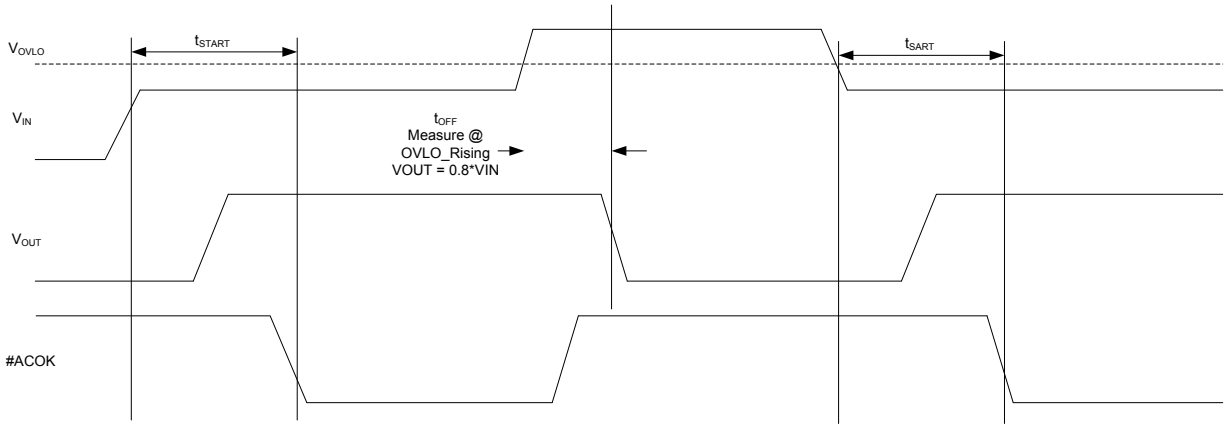
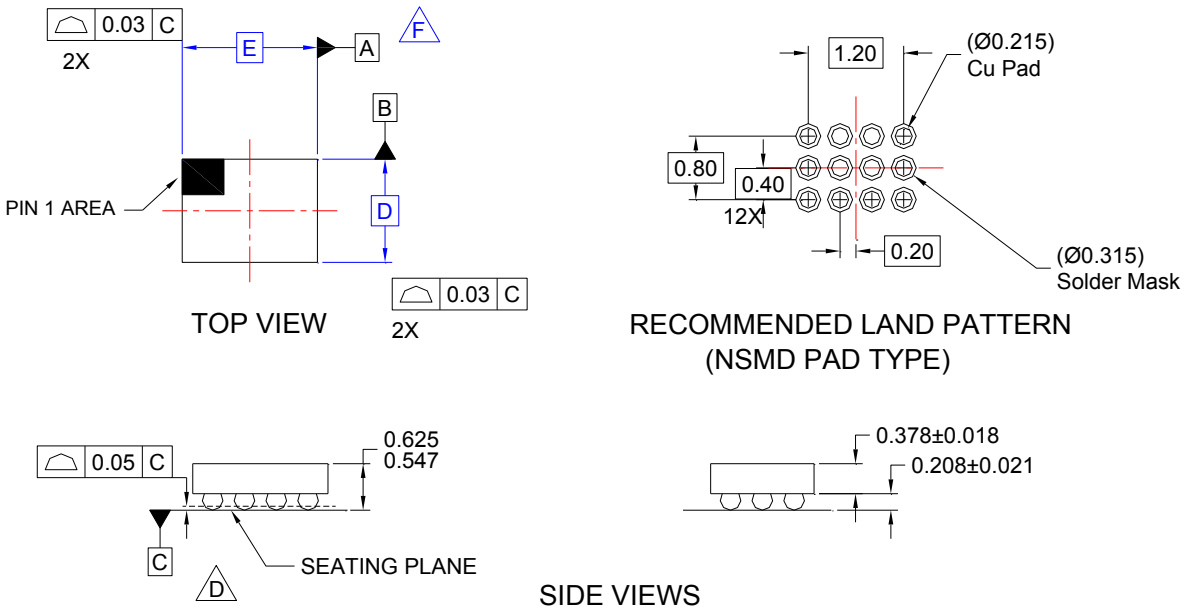


Figure 5. Timing for OVLO Trip

Product-Specific Package Dimensions

D	E	X	Y
1288 µm ±30 µm	1828 µm ±30 µm	314 µm ±18 µm	244 µm ±18 µm

Physical Dimensions



NOTES:

A. NO JEDEC REGISTRATION APPLIES.

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. DATUM C IS DEFINED BY THE SPHERICAL CROWNS OF THE BALLS.

E. PACKAGE NOMINAL HEIGHT IS 586 MICRONS ±39 MICRONS (547-625 MICRONS).

F. FOR DIMENSIONS D, E, X, AND Y SEE PRODUCT DATASHEET.

G. DRAWING FILENAME: MKT-UC012ZCrev2..

H. ON SEMICONDUCTOR RECOMMENDS THAT LANDS IN THE LANDPATTERN ARE AT LEAST .215MM DIAMETER AS MEASURED AT THE BOTTOM OF THE LAND, NOT THE TOP EDGE

Figure 6. 12-Ball, 3×4 Array, 0.4 mm Pitch, Wafer-Level Chip-Scale Package (WLCSP)

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
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